

**IN SITU APPLICATION OF ETCH BACK FOR IMPROVED DEPOSITION
INTO HIGH-ASPECT-RATIO FEATURES**

ABSTRACT OF THE DISCLOSURE

5 A continuous *in situ* process of deposition, etching, and deposition is
provided for forming a film on a substrate using a plasma process. The etch-back may
be performed without separate plasma activation of the etchant gas. The sequence of
deposition, etching, and deposition permits features with high aspect ratios to be filled,
while the continuity of the process results in improved uniformity.

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